

CPC COOPERATIVE PATENT CLASSIFICATION

C CHEMISTRY; METALLURGY

(NOTES omitted)

METALLURGY

C30 CRYSTAL GROWTH

C30B SINGLE-CRYSTAL GROWTH (by using ultra-high pressure, e.g. for the formation of diamonds, [B01J 3/06](#)); **UNIDIRECTIONAL SOLIDIFICATION OF EUTECTIC MATERIAL OR UNIDIRECTIONAL DEMIXING OF EUTECTOID MATERIAL; REFINING BY ZONE-MELTING OF MATERIAL** (zone-refining of metals or alloys [C22B](#)); **PRODUCTION OF A HOMOGENEOUS POLYCRYSTALLINE MATERIAL WITH DEFINED STRUCTURE** (casting of metals, casting of other substances by the same processes or devices [B22D](#); working of plastics [B29](#); modifying the physical structure of metals or alloys [C21D](#), [C22F](#)); **SINGLE CRYSTALS OR HOMOGENEOUS POLYCRYSTALLINE MATERIAL WITH DEFINED STRUCTURE; AFTER-TREATMENT OF SINGLE CRYSTALS OR A HOMOGENEOUS POLYCRYSTALLINE MATERIAL WITH DEFINED STRUCTURE** (for producing semiconductor devices or parts thereof [H01L](#)); **APPARATUS THEREFOR**

NOTES

- In this subclass, the following expressions are used with the meaning indicated:
 - "single-crystal" includes also twin crystals and a predominantly single crystal product;
 - "homogeneous polycrystalline material" means a material with crystal particles, all of which have the same chemical composition;
 - "defined structure" means the structure of a material with grains which are oriented in a preferential way or have larger dimensions than normally obtained.
- In this subclass:
 - the preparation of crystals or a homogeneous polycrystalline material with defined structure of particular materials or shapes is classified in the group for the process as well as in group [C30B 29/00](#);
 - an apparatus specially adapted for a specific process is classified in the appropriate group for the process. Apparatus to be used in more than one kind of process is classified in group [C30B 35/00](#).

WARNING

In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.

Single-crystal growth from solids or gels

- 1/00 Single-crystal growth directly from the solid state** (unidirectional demixing of eutectoid materials [C30B 3/00](#); under a protective fluid [C30B 27/00](#))
- 1/02 . by thermal treatment, e.g. strain annealing ([C30B 1/12](#) takes precedence)
- 1/023 . . {from solids with amorphous structure}
- 1/026 . . {Solid phase epitaxial growth through a disordered intermediate layer}
- 1/04 . . Isothermal recrystallisation
- 1/06 . . Recrystallisation under a temperature gradient
- 1/08 . . . Zone recrystallisation
- 1/10 . by solid state reactions or multi-phase diffusion
- 1/12 . by pressure treatment during the growth
- 3/00 Unidirectional demixing of eutectoid materials**
- 5/00 Single-crystal growth from gels** (under a protective fluid [C30B 27/00](#))

5/02 . with addition of doping materials

Single-crystal growth from liquids; Unidirectional solidification of eutectic materials

- 7/00 Single-crystal growth from solutions using solvents which are liquid at normal temperature, e.g. aqueous solutions** (from molten solvents [C30B 9/00](#); by normal or gradient freezing [C30B 11/00](#); under a protective fluid [C30B 27/00](#))
- 7/005 . {Epitaxial layer growth}
- 7/02 . by evaporation of the solvent
- 7/04 . . using aqueous solvents
- 7/06 . . using non-aqueous solvents
- 7/08 . by cooling of the solution
- 7/10 . by application of pressure, e.g. hydrothermal processes
- 7/105 . . {using ammonia as solvent, i.e. ammonothermal processes}

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| 7/12 | • by electrolysis | 13/14 | • Crucibles or vessels |
| 7/14 | • the crystallising materials being formed by chemical reactions in the solution | 13/16 | • Heating of the molten zone |
| | | 13/18 | • • the heating element being in contact with, or immersed in, the molten zone |
| 9/00 | Single-crystal growth from melt solutions using molten solvents (by normal or gradient freezing C30B 11/00 ; by zone-melting C30B 13/00 ; by crystal pulling C30B 15/00 ; on immersed seed crystal C30B 17/00 ; by liquid phase epitaxial growth C30B 19/00 ; under a protective fluid C30B 27/00) | 13/20 | • • by induction, e.g. hot wire technique (C30B 13/18 takes precedence) |
| 9/02 | • by evaporation of the molten solvent | 13/22 | • • by irradiation or electric discharge |
| 9/04 | • by cooling of the solution | 13/24 | • • • using electromagnetic waves |
| 9/06 | • • using as solvent a component of the crystal composition | 13/26 | • Stirring of the molten zone |
| 9/08 | • • using other solvents | 13/28 | • Controlling or regulating |
| 9/10 | • • • Metal solvents | 13/285 | • • {Crystal holders, e.g. chucks} |
| 9/12 | • • • Salt solvents, e.g. flux growth | 13/30 | • • Stabilisation or shape controlling of the molten zone, e.g. by concentrators, by electromagnetic fields; Controlling the section of the crystal |
| 9/14 | • by electrolysis | 13/32 | • Mechanisms for moving either the charge or the heater |
| | | 13/34 | • characterised by the seed, e.g. by its crystallographic orientation |
| 11/00 | Single-crystal growth by normal freezing or freezing under temperature gradient, e.g. Bridgman-Stockbarger method (C30B 13/00 , C30B 15/00 , C30B 17/00 , C30B 19/00 take precedence; under a protective fluid C30B 27/00) | 15/00 | Single-crystal growth by pulling from a melt, e.g. Czochralski method (under a protective fluid C30B 27/00) |
| 11/001 | • {Continuous growth} | 15/002 | • {Continuous growth} |
| 11/002 | • {Crucibles or containers for supporting the melt} | 15/005 | • {Simultaneous pulling of more than one crystal} |
| 11/003 | • {Heating or cooling of the melt or the crystallised material} | 15/007 | • {Pulling on a substrate} |
| 11/005 | • {by irradiation or electric discharge} | 15/02 | • adding crystallising materials or reactants forming it <u>in situ</u> to the melt |
| 11/006 | • {Controlling or regulating} | 15/04 | • • adding doping materials, e.g. for n-p-junction |
| 11/007 | • {Mechanisms for moving either the charge or the heater} | 15/06 | • Non-vertical pulling |
| 11/008 | • {using centrifugal force to the charge} | 15/08 | • Downward pulling |
| 11/02 | • without using solvents (C30B 11/06 takes precedence) | 15/10 | • Crucibles or containers for supporting the melt |
| 11/04 | • adding crystallising materials or reactants forming it <u>in situ</u> to the melt | 15/12 | • • Double crucible methods |
| 11/06 | • • at least one but not all components of the crystal composition being added | 15/14 | • Heating of the melt or the crystallised materials |
| 11/065 | • • • {before crystallising, e.g. synthesis} | 15/16 | • • by irradiation or electric discharge |
| 11/08 | • • every component of the crystal composition being added during the crystallisation | 15/18 | • • using direct resistance heating in addition to other methods of heating, e.g. using Peltier heat |
| 11/10 | • • • Solid or liquid components, e.g. Verneuil method | 15/20 | • Controlling or regulating (controlling or regulating in general G05) |
| 11/12 | • • • Vaporous components, e.g. vapour-liquid-solid-growth | 15/203 | • • {the relationship of pull rate (v) to axial thermal gradient (G)} |
| 11/14 | • characterised by the seed, e.g. its crystallographic orientation | 15/206 | • • {the thermal history of growing the ingot} |
| | | 15/22 | • • Stabilisation or shape controlling of the molten zone near the pulled crystal; Controlling the section of the crystal |
| 13/00 | Single-crystal growth by zone-melting; Refining by zone-melting (C30B 17/00 takes precedence; by changing the cross-section of the treated solid C30B 15/00 ; under a protective fluid C30B 27/00 ; zone-refining of specific materials, see the relevant subclasses for the materials) | 15/24 | • • • using mechanical means, e.g. shaping guides (shaping dies for edge-defined film-fed crystal growth C30B 15/34) |
| 13/005 | • {Continuous growth} | 15/26 | • • • using television detectors; using photo or X-ray detectors |
| 13/02 | • Zone-melting with a solvent, e.g. travelling solvent process | 15/28 | • • • using weight changes of the crystal or the melt, e.g. flotation methods |
| 13/04 | • Homogenisation by zone-levelling | 15/30 | • Mechanisms for rotating or moving either the melt or the crystal (flotation methods C30B 15/28) |
| 13/06 | • the molten zone not extending over the whole cross-section | 15/305 | • • {Stirring of the melt} |
| 13/08 | • adding crystallising materials or reactants forming it <u>in situ</u> to the molten zone | 15/32 | • Seed holders, e.g. chucks |
| 13/10 | • • with addition of doping materials | 15/34 | • Edge-defined film-fed crystal-growth using dies or slits |
| 13/12 | • • • in the gaseous or vapour state | 15/36 | • characterised by the seed, e.g. its crystallographic orientation |
| | | 17/00 | Single-crystal growth onto a seed which remains in the melt during growth, e.g. Nacken-Kyropoulos method (C30B 15/00 takes precedence) |
| | | 19/00 | Liquid-phase epitaxial-layer growth |

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| 19/02 | . using molten solvents, e.g. flux | 25/16 | . . Controlling or regulating (controlling or regulating in general G05) |
| 19/04 | . . the solvent being a component of the crystal composition | 25/165 | . . . {the flow of the reactive gases} |
| 19/06 | . Reaction chambers; Boats for supporting the melt; Substrate holders | 25/18 | . . characterised by the substrate |
| 19/061 | . . {Tipping system, e.g. by rotation} | 25/183 | . . . {being provided with a buffer layer, e.g. a lattice matching layer} |
| 19/062 | . . {Vertical dipping system} | 25/186 | . . . {being specially pre-treated by, e.g. chemical or physical means} |
| 19/063 | . . {Sliding boat system} | 25/20 | . . . the substrate being of the same materials as the epitaxial layer |
| 19/064 | . . {Rotating sliding boat system} | 25/205 | {the substrate being of insulating material} |
| 19/065 | . . {Multiple stacked slider system} | 25/22 | . . Sandwich processes |
| 19/066 | . . {Injection or centrifugal force system} | 27/00 | Single-crystal growth under a protective fluid |
| 19/067 | . . {Boots or containers} | 27/02 | . by pulling from a melt |
| 19/068 | . . {Substrate holders} | 28/00 | Production of homogeneous polycrystalline material with defined structure |
| 19/08 | . Heating of the reaction chamber or the substrate | 28/02 | . directly from the solid state |
| 19/10 | . Controlling or regulating (controlling or regulating in general G05) | 28/04 | . from liquids |
| 19/103 | . . {Current controlled or induced growth} | 28/06 | . . by normal freezing or freezing under temperature gradient |
| 19/106 | . . {adding crystallising material or reactants forming it <i>in situ</i> to the liquid} | 28/08 | . . by zone-melting |
| 19/12 | . characterised by the substrate | 28/10 | . . by pulling from a melt |
| 21/00 | Unidirectional solidification of eutectic materials | 28/12 | . directly from the gas state |
| 21/02 | . by normal casting or gradient freezing | 28/14 | . . by chemical reaction of reactive gases |
| 21/04 | . by zone-melting | 29/00 | Single crystals or homogeneous polycrystalline material with defined structure characterised by the material or by their shape |
| 21/06 | . by pulling from a melt | | NOTE |
| Single-crystal growth from vapours | | | In groups C30B 29/02 - C30B 29/58 , in the absence of an indication to the contrary, a material is classified in the last appropriate place. |
| 23/00 | Single-crystal growth by condensing evaporated or sublimed materials | | |
| | NOTE | | |
| | Groups C30B 23/002 - C30B 23/005 take precedence over groups C30B 23/007 - C30B 23/08 | | |
| 23/002 | . {Controlling or regulating} | 29/02 | . Elements |
| 23/005 | . . {Controlling or regulating flux or flow of depositing species or vapour} | 29/04 | . . Diamond |
| 23/007 | . {Growth of whiskers or needles} | 29/06 | . . Silicon |
| 23/02 | . Epitaxial-layer growth | 29/08 | . . Germanium |
| 23/025 | . . {characterised by the substrate} | 29/10 | . Inorganic compounds or compositions |
| 23/04 | . . Pattern deposit, e.g. by using masks | 29/12 | . . Halides |
| 23/06 | . . Heating of the deposition chamber, the substrate or the materials to be evaporated | 29/14 | . . Phosphates |
| 23/063 | . . . {Heating of the substrate} | 29/16 | . . Oxides |
| 23/066 | . . . {Heating of the material to be evaporated} | 29/18 | . . . Quartz |
| 23/08 | . . by condensing ionised vapours (by reactive sputtering C30B 25/06) | 29/20 | . . . Aluminium oxides |
| 25/00 | Single-crystal growth by chemical reaction of reactive gases, e.g. chemical vapour-deposition growth | 29/22 | . . . Complex oxides |
| 25/005 | . {Growth of whiskers or needles} | 29/225 | {based on rare earth copper oxides, e.g. high T-superconductors} |
| 25/02 | . Epitaxial-layer growth | 29/24 | with formula $AMeO_3$, wherein A is a rare earth metal and Me is Fe, Ga, Sc, Cr, Co or Al, e.g. ortho ferrites |
| 25/025 | . . {Continuous growth} | 29/26 | with formula BMe_2O_4 , wherein B is Mg, Ni, Co, Al, Zn, or Cd and Me is Fe, Ga, Sc, Cr, Co, or Al |
| 25/04 | . . Pattern deposit, e.g. by using masks | 29/28 | with formula $A_3Me_5O_{12}$ wherein A is a rare earth metal and Me is Fe, Ga, Sc, Cr, Co or Al, e.g. garnets |
| 25/06 | . . by reactive sputtering | 29/30 | Niobates; Vanadates; Tantalates |
| 25/08 | . . Reaction chambers; Selection of materials therefor | 29/32 | Titanates; Germanates; Molybdates; Tungstates |
| 25/10 | . . Heating of the reaction chamber or the substrate | 29/34 | . . Silicates |
| 25/105 | . . . {by irradiation or electric discharge} | 29/36 | . . Carbides |
| 25/12 | . . Substrate holders or susceptors | 29/38 | . . Nitrides |
| 25/14 | . . Feed and outlet means for the gases; Modifying the flow of the reactive gases | | |

- 29/40 . . $A_{III}B_V$ compounds {wherein A is B, Al, Ga, In or Tl and B is N, P, As, Sb or Bi}
- 29/403 . . . { A_{III} -nitrides}
- 29/406 . . . {Gallium nitride}
- 29/42 . . . Gallium arsenide
- 29/44 . . . Gallium phosphide
- 29/46 . . Sulfur-, selenium- or tellurium-containing compounds
- 29/48 . . . $A_{II}B_{VI}$ compounds {wherein A is Zn, Cd or Hg, and B is S, Se or Te}
- 29/50 Cadmium sulfide
- 29/52 . . Alloys
- 29/54 . Organic compounds
- 29/56 . . Tartrates
- 29/58 . . Macromolecular compounds
- 29/60 . characterised by shape
- 29/602 . . {Nanotubes}
- 29/605 . . {Products containing multiple oriented crystallites, e.g. columnar crystallites}
- 29/62 . . Whiskers or needles
- 29/64 . . Flat crystals, e.g. plates, strips or discs
- 29/66 . . Crystals of complex geometrical shape, e.g. tubes, cylinders
- 29/68 . . Crystals with laminate structure, e.g. "superlattices"

30/00 Production of single crystals or homogeneous polycrystalline material with defined structure characterised by the action of electric or magnetic fields, wave energy or other specific physical conditions

NOTE

When classifying in this group, classification is also made in groups [C30B 1/00](#) - [C30B 27/00](#) according to the process of crystal growth.

- 30/02 . using electric fields, e.g. electrolysis
- 30/04 . using magnetic fields
- 30/06 . using mechanical vibrations
- 30/08 . in conditions of zero-gravity or low gravity

After-treatment of single crystals or homogeneous polycrystalline material with defined structure

- 31/00 Diffusion or doping processes for single crystals or homogeneous polycrystalline material with defined structure; Apparatus therefor**
- 31/02 . by contacting with diffusion materials in the solid state
- 31/04 . by contacting with diffusion materials in the liquid state
- 31/045 . . {by electrolysis}
- 31/06 . by contacting with diffusion material in the gaseous state
- 31/08 . . the diffusion materials being a compound of the elements to be diffused
- 31/10 . . Reaction chambers; Selection of materials therefor
- 31/103 . . . {Mechanisms for moving either the charge or heater}
- 31/106 . . . {Continuous processes}
- 31/12 . . Heating of the reaction chamber
- 31/14 . . Substrate holders or susceptors

- 31/16 . . Feed and outlet means for the gases; Modifying the flow of the gases
- 31/165 . . . {Diffusion sources}
- 31/18 . . Controlling or regulating
- 31/185 . . . {Pattern diffusion, e.g. by using masks}
- 31/20 . Doping by irradiation with electromagnetic waves or by particle radiation
- 31/22 . . by ion-implantation
- 33/00 After-treatment of single crystals or homogeneous polycrystalline material with defined structure ([C30B 31/00](#) takes precedence)**
- 33/005 . {Oxydation}
- 33/02 . Heat treatment ([C30B 33/04](#), [C30B 33/06](#) take precedence)
- 33/04 . using electric or magnetic fields or particle radiation
- 33/06 . Joining of crystals
- 33/08 . Etching
- 33/10 . . in solutions or melts
- 33/12 . . in gas atmosphere or plasma
- 35/00 Apparatus not otherwise provided for, specially adapted for the growth, production or after-treatment of single crystals or of a homogeneous polycrystalline material with defined structure**
- 35/002 . {Crucibles or containers}
- 35/005 . {Transport systems}
- 35/007 . {Apparatus for preparing, pre-treating the source material to be used for crystal growth}